

PMWD26UN

Dual μ TrenchMOS™ ultra low level FET

Rev. 01 — 22 January 2003

Product data

1. Product profile

1.1 Description

Dual N-channel enhancement mode field-effect transistor in a plastic package using TrenchMOS™ technology.

Product availability:

PMWD26UN in SOT530-1 (TSSOP8).

1.2 Features

- Surface mounting package
- Very low threshold
- Low profile
- Fast switching.

1.3 Applications

- Portable appliances
- Battery management
- PCMCIA cards
- Load switching.

1.4 Quick reference data

- $V_{DS} \leq 20$ V
- $P_{tot} \leq 2.3$ W
- $I_D \leq 5.2$ A
- $R_{DSon} \leq 30$ m Ω

2. Pinning information

Table 1: Pinning - SOT530-1, simplified outline and symbol

Pin	Description	Simplified outline	Symbol
1	drain1 (d1)	<p>Top view MBK885</p> <p>SOT530-1</p>	
2,3	source1 (s1)		
4	gate1 (g1)		
5	gate2 (g2)		
6,7	source2 (s2)		
8	drain2 (d2)		



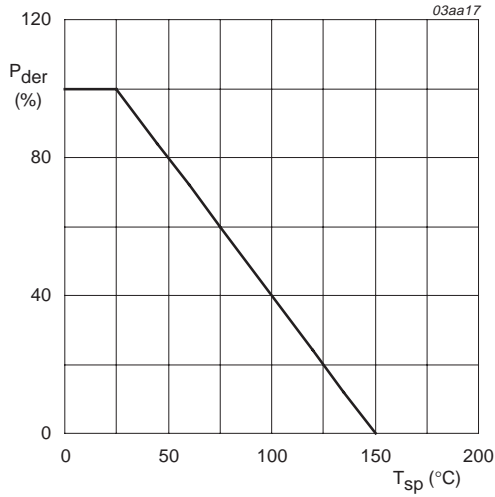
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3. Limiting values

Table 2: Limiting values

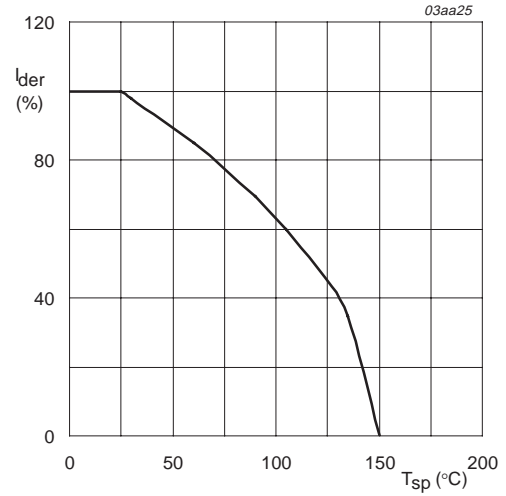
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)	$25\text{ °C} \leq T_j \leq 150\text{ °C}$	-	20	V
V_{DGR}	drain-gate voltage	$25\text{ °C} \leq T_j \leq 150\text{ °C}$; $R_{GS} = 20\text{ k}\Omega$	-	20	V
V_{GS}	gate-source voltage		-	± 10	V
I_D	drain current (DC)	$T_{sp} = 25\text{ °C}$; $V_{GS} = 4.5\text{ V}$; Figure 2 and 3	-	5.2	A
		$T_{sp} = 100\text{ °C}$; $V_{GS} = 4.5\text{ V}$; Figure 2	-	3.1	A
I_{DM}	peak drain current	$T_{sp} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; Figure 3	-	18	A
P_{tot}	total power dissipation	$T_{sp} = 25\text{ °C}$; Figure 1	-	2.3	W
T_{stg}	storage temperature		-55	+150	°C
T_j	junction temperature		-55	+150	°C
Source-drain diode					
I_S	source (diode forward) current (DC)	$T_{sp} = 25\text{ °C}$	-	2	A
I_{SM}	peak source (diode forward) current	$T_{sp} = 25\text{ °C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$	-	7	A



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

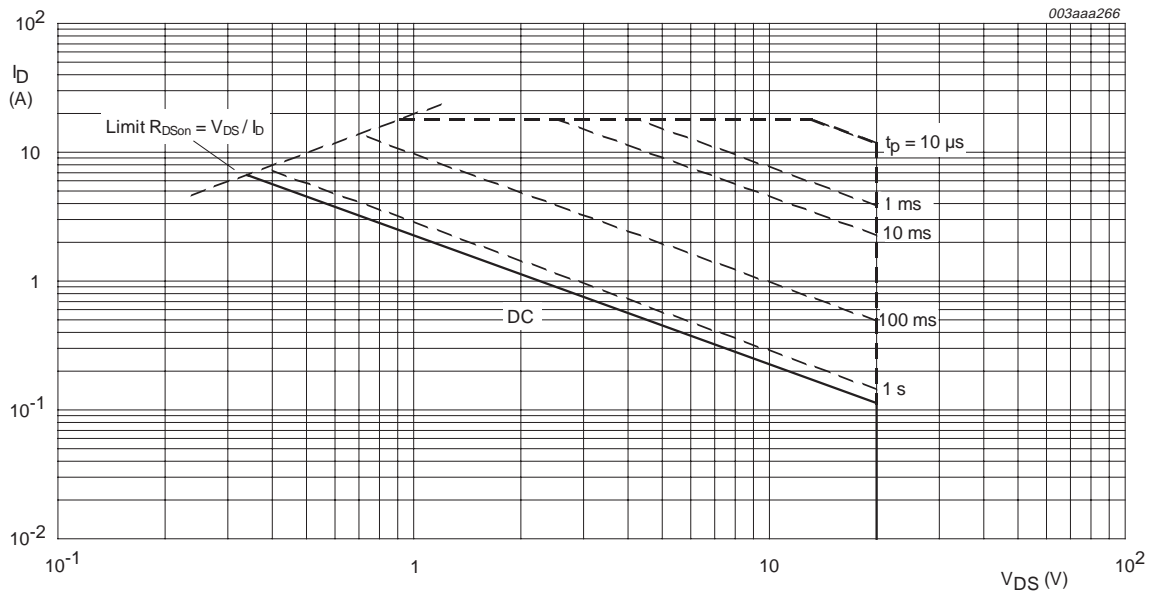
Fig 1. Normalized total power dissipation as a function of solder point temperature.



$V_{GS} \geq 4.5\text{ V}$

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of solder point temperature.



$T_{sp} = 25^{\circ}C$; I_{DM} is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

4. Thermal characteristics

Table 3: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	Figure 4	-	55	70	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; mounted on printed-circuit board	-	100	-	K/W

4.1 Transient thermal impedance

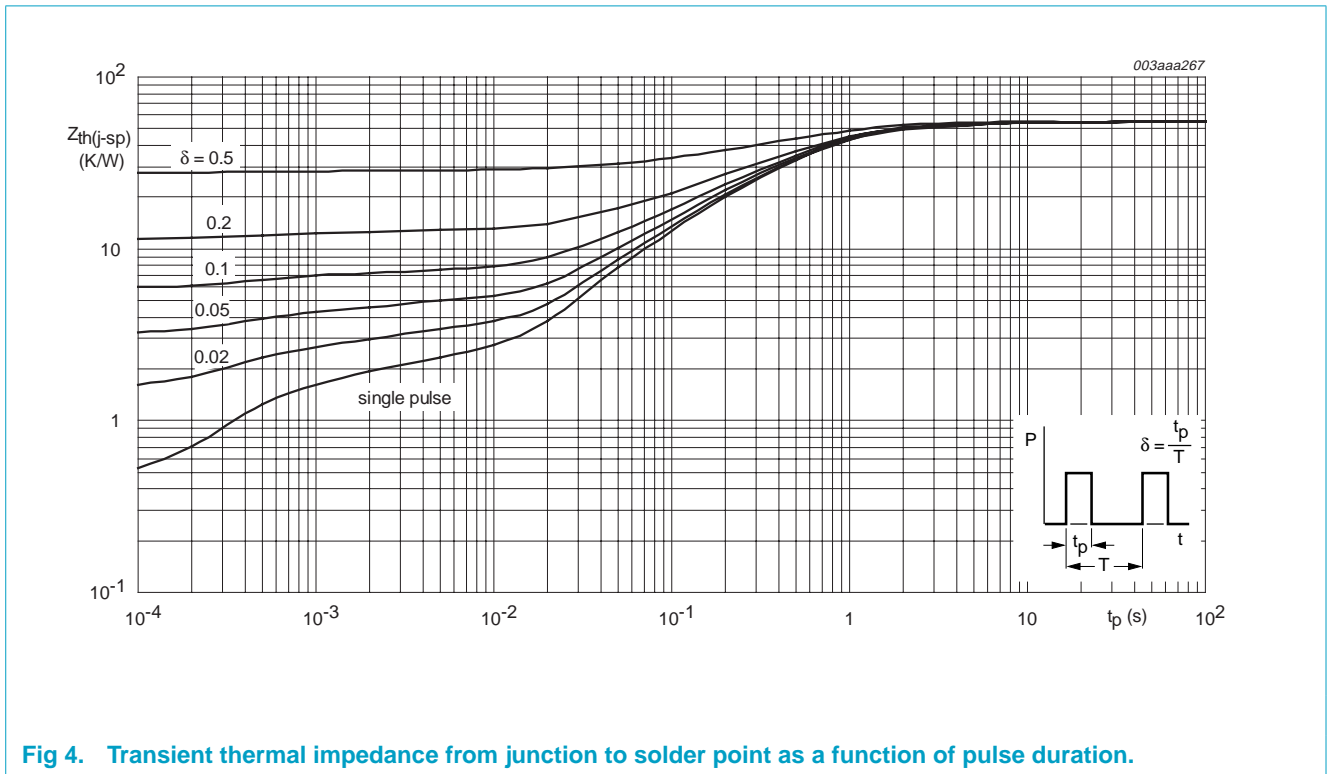
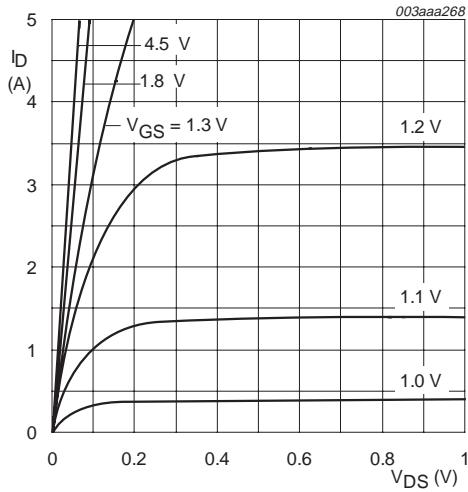


Fig 4. Transient thermal impedance from junction to solder point as a function of pulse duration.

5. Characteristics

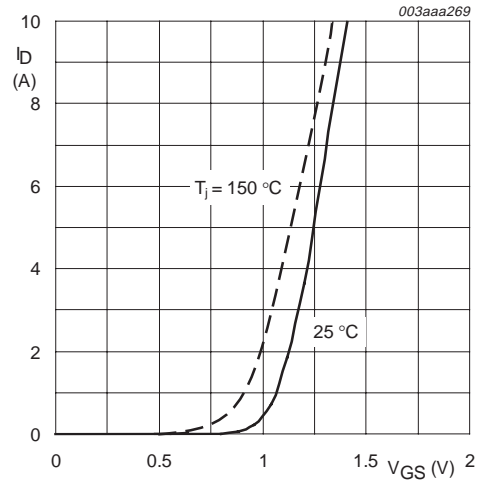
Table 4: Characteristics
 $T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}$; $V_{GS} = 0\text{ V}$ $T_j = 25\text{ }^\circ\text{C}$	20	-	-	V
		$T_j = -55\text{ }^\circ\text{C}$	18	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\text{ mA}$; $V_{DS} = V_{GS}$; Figure 9	0.45	0.7	-	V
I_{DSS}	drain-source leakage current	$V_{DS} = 20\text{ V}$; $V_{GS} = 0\text{ V}$ $T_j = 25\text{ }^\circ\text{C}$	-	-	1	μA
		$T_j = 150\text{ }^\circ\text{C}$	-	-	100	μA
I_{GSS}	gate-source leakage current	$V_{GS} = \pm 10\text{ V}$; $V_{DS} = 0\text{ V}$	-	-	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}$; $I_D = 3.5\text{ A}$; Figure 7 and 8 $T_j = 25\text{ }^\circ\text{C}$	-	26	30	m Ω
		$T_j = 150\text{ }^\circ\text{C}$	-	44	51	m Ω
		$V_{GS} = 1.8\text{ V}$; $I_D = 3.5\text{ A}$; Figure 7	-	34	40	m Ω
		$V_{GS} = 2.5\text{ V}$; $I_D = 3.5\text{ A}$; Figure 7	-	29	35	m Ω
Dynamic characteristics						
$Q_{g(tot)}$	total gate charge	$I_D = 4\text{ A}$; $V_{DD} = 16\text{ V}$; $V_{GS} = 4.5\text{ V}$; Figure 13	-	23.6	-	nC
Q_{gs}	gate-source charge		-	2.1	-	nC
Q_{gd}	gate-drain (Miller) charge		-	6.7	-	nC
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}$; $V_{DS} = 16\text{ V}$; $f = 1\text{ MHz}$; Figure 11	-	1366	-	pF
C_{oss}	output capacitance		-	339	-	pF
C_{riss}	reverse transfer capacitance		-	239	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DD} = 10\text{ V}$; $I_D = 1\text{ A}$; $V_{GS} = 4.5\text{ V}$; $R_G = 6\text{ }\Omega$	-	14	-	ns
t_r	rise time		-	22	-	ns
$t_{d(off)}$	turn-off delay time		-	56	-	ns
t_f	fall time		-	33	-	ns
Source-drain diode						
V_{SD}	source-drain (diode forward) voltage	$I_S = 4\text{ A}$; $V_{GS} = 0\text{ V}$; Figure 12	-	0.67	1.2	V
t_{rr}	reverse recovery time	$I_S = 4\text{ A}$; $di_S/dt = -100\text{ A}/\mu\text{s}$; $V_R = 20\text{ V}$;	-	45	-	ns
Q_r	recovered charge	$V_{GS} = 0\text{ V}$	-	13	-	nC



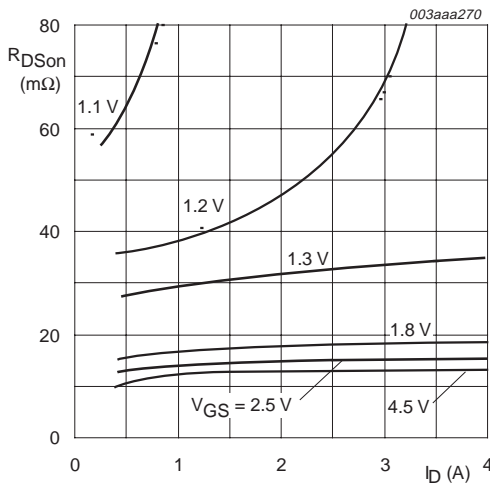
$T_j = 25\text{ }^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.



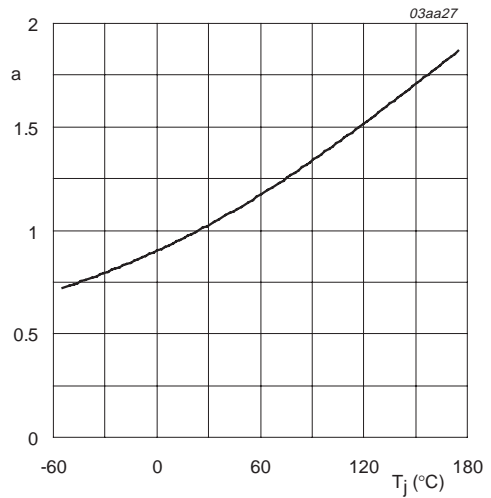
$T_j = 25\text{ }^\circ\text{C}$ and $150\text{ }^\circ\text{C}$; $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



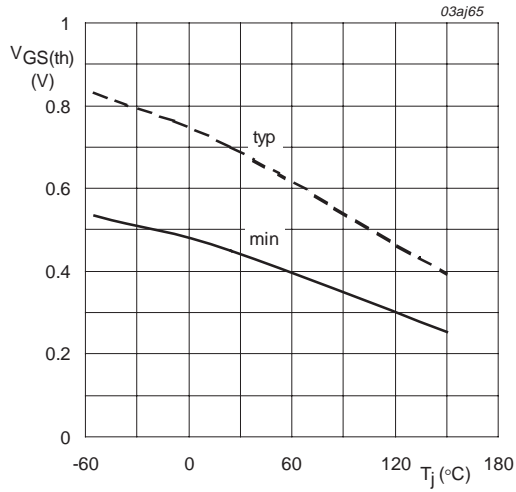
$T_j = 25\text{ }^\circ\text{C}$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



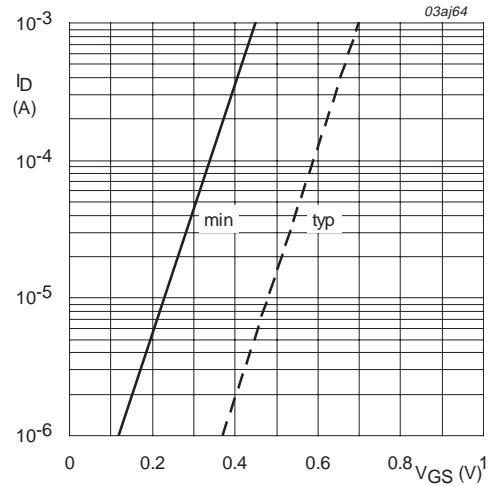
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 8. Normalized drain source on-state resistance factor as a function of junction temperature.



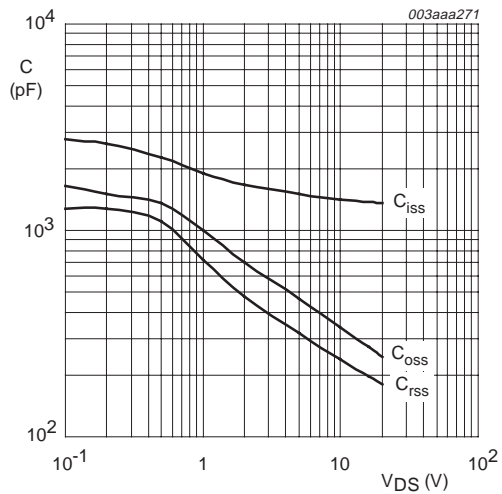
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature.



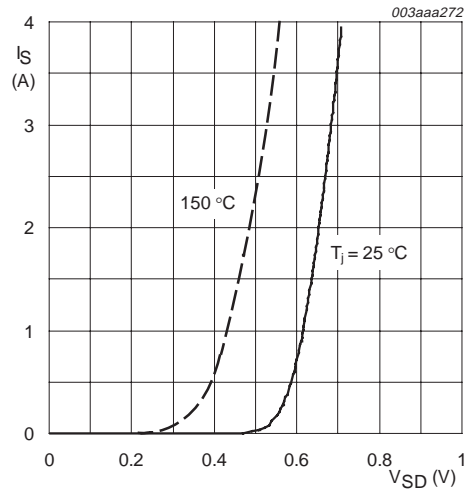
$T_j = 25 \text{ }^{\circ}C; V_{DS} = 5 \text{ V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage.



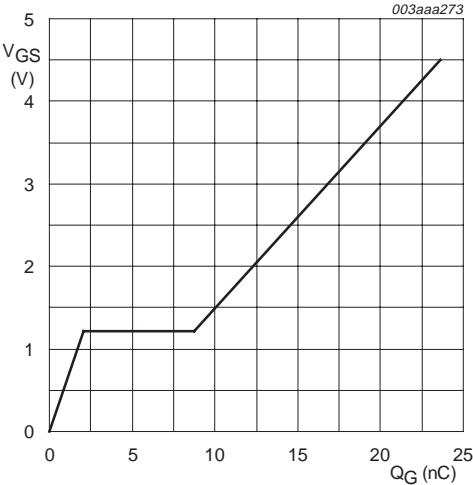
$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

Fig 11. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



$T_j = 25 \text{ }^{\circ}C \text{ and } 150 \text{ }^{\circ}C; V_{GS} = 0 \text{ V}$

Fig 12. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.



$I_D = 4 \text{ A}; V_{DD} = 16 \text{ V}$

Fig 13. Gate-source voltage as a function of gate charge; typical values.

6. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 4.4 mm

SOT530-1

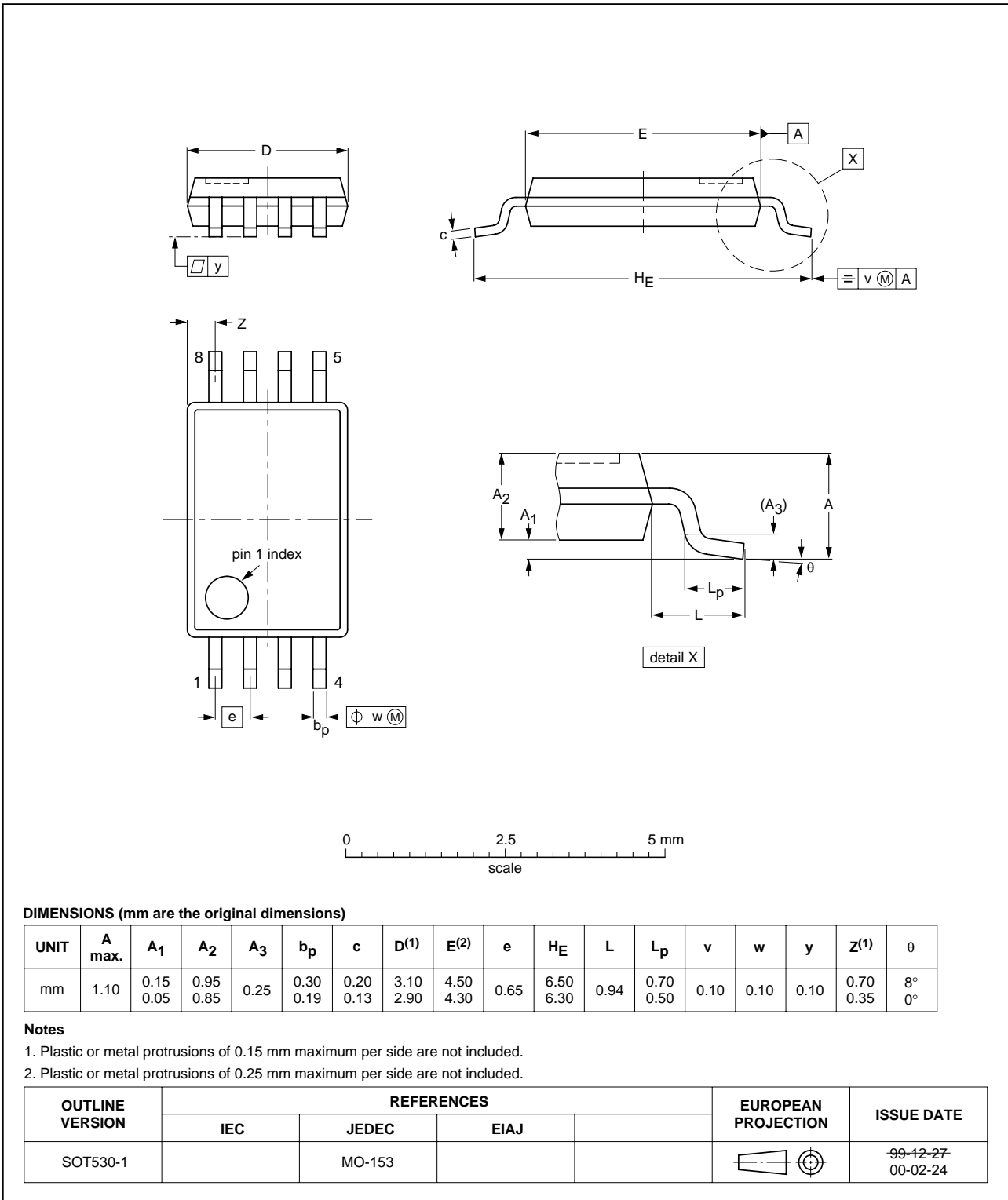


Fig 14. SOT530-1 (TSSOP8).

7. Revision history

Table 5: Revision history

Rev	Date	CPCN	Description
01	20030122	-	Product data (9397 750 10834)

8. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2][3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Contact information

For additional information, please visit <http://www.semiconductors.philips.com>.

For sales office addresses, send e-mail to: sales.addresses@www.semiconductors.philips.com.

Fax: +31 40 27 24825

Contents

1	Product profile	1
1.1	Description	1
1.2	Features	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	1
3	Limiting values	2
4	Thermal characteristics	4
4.1	Transient thermal impedance	4
5	Characteristics	5
6	Package outline	9
7	Revision history	10
8	Data sheet status	11
9	Definitions	11
10	Disclaimers	11
11	Trademarks	11

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